

M210 TYPE 12BB Data Sheet



Extremely low light-induced degradation



Strong low-light response



Low temperature poly-Si deposition process



Advanced Laser-enhanced contact optimization



Extremely low light-induced degradation



High module sealed power



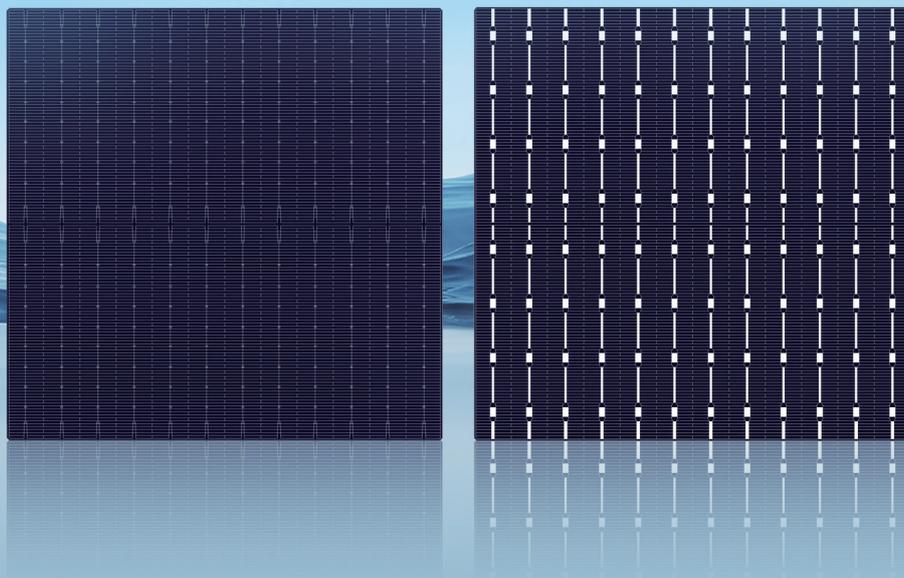
Advanced passivation & doping technology



Strong weather resistance



Extremely low light-induced degradation



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TECHNICAL CHARACTERISTICS

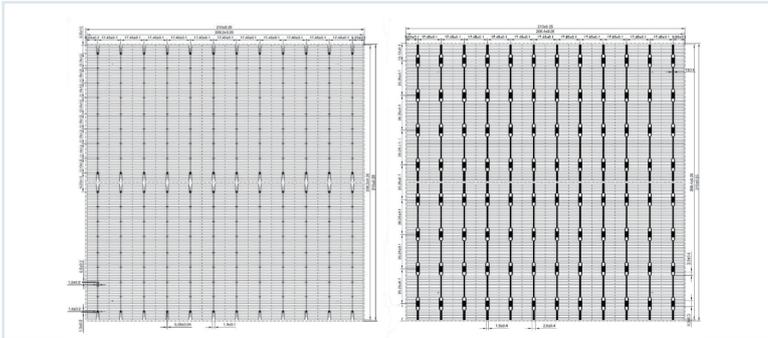
Dimension	210mm*210mm±0.25mm	TkVoltage:-0.36%/K
Thickness	180±18um	TkCurrent:+0.07%/K
Front	12*0.08+0.04mm main bus bar (silver) 168+15 auxiliary bus bar, blue (dark blue) anti-reflective film (silicon nitride)	TkPower:-0.38%/K
Back(+)	Back electrode width (silver) 2.2+0.4mm back covered with aluminum bus bar	Rsh≥35Ω,Irev2≤0.8A

LIGHT INTENSITY AND RELIABILITY

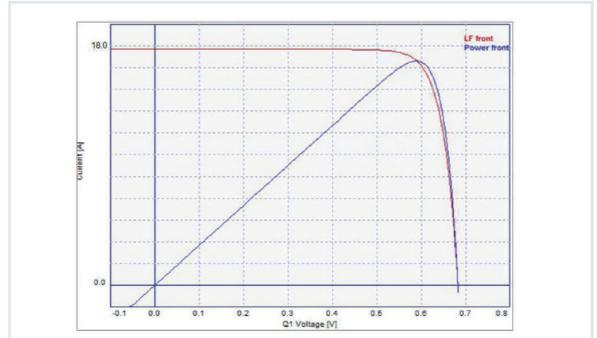
Intensity(W/m ²)	Voc	Isc
1000	1.000	1.000
900	0.996	0.903
800	0.991	0.803
600	0.988	0.602
400	0.962	0.403

The Voc(Isc) tested by 1000W/m² is the standard, and the Voc(Isc) decreases with the strong decrease in light.

PRINTING GRAPHICS



IV CURVE



WELDABILITY Minimum peeling intensity ≥1.0N/mm Results may vary depending on the welding ribbon, welding methods and conditions.

ELECTRICAL CHARACTERISTICS

Eff(%)	Pmpp(W)	FF(%)	I _{mp} (A)	V _{mp} (V)	I _{sc} (A)	V _{oc} (V)
23.0	10.14	81.51	17.517	0.579	18.325	0.679
22.9	10.10	81.40	17.471	0.578	18.297	0.678
22.8	10.06	81.30	17.394	0.578	18.240	0.678
22.7	10.01	81.19	17.348	0.577	18.211	0.677
22.6	9.97	81.18	17.302	0.576	18.187	0.675
22.5	9.92	81.18	17.285	0.574	18.160	0.673
22.4	9.88	81.17	17.328	0.573	18.108	0.672
22.3	9.83	81.17	17.161	0.573	18.108	0.669
22.2	9.79	81.16	17.114	0.572	18.057	0.668
22.1	9.75	81.14	17.037	0.572	17.980	0.668
22.0	9.70	81.05	16.960	0.572	17.945	0.667
21.9	9.66	80.94	16.912	0.571	17.888	0.667

STC:1000W/m², AM1.5, 25°C/Specifications and data for reference only.